



#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
	12mΩ @ V <sub>GS</sub> = 10V	10A
30V	16mΩ @ V <sub>GS</sub> = 4.5V	8.5A

### **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(on)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management Application
- Power Management Functions
- DC-DC Converters

## **Features and Benefits**

- 0.6mm profile ideal for low profile applications
- PCB footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

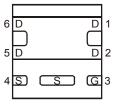
#### **Mechanical Data**

- Case: U-DFN2020-6 Type E
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (approximate)

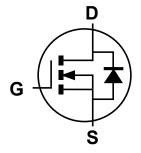
#### U-DFN2020-6 Type E







Pin Out



Internal Schematic

#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3016LFDE-7	U-DFN2020-6 Type E	3,000/Tape & Reel
DMN3016LFDE-13	U-DFN2020-6 Type E	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



NR = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011) M = Month (ex: 9 = September)

#### Date Code Kev

Year	201	1	2012		2013	20	14	2015		2016	2	2017
Code	Υ		Z		Α	E	3	С		D		E
						•					•	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



#### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		$V_{DSS}$	30	V	
Gate-Source Voltage		$V_{GSS}$	±20	V	
Continuous Prain Current (Note 6) / - 40)/	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	10 8	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	12 9	А
Maximum Continuous Body Diode Forward Curren	t (Note 6)		I <sub>S</sub>	2.5	Α
Pulsed Drain Current (10μs pulse, duty cycle = 1%	)	I <sub>DM</sub>	90	Α	
Avalanche Current (Note 7) L = 0.1mH		I <sub>AR</sub>	22	Α	
Repetitive Avalanche Energy (Note 7) L = 0.1mH		E <sub>AR</sub>	24	mJ	

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	П	0.73	W	
Total Fower Dissipation (Note 5)	T <sub>A</sub> = +70°C	$P_{D}$	0.47		
Thermal Desigtance Junction to Ambient (Note 5)	Steady state		171	°C/M	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	121	°C/W	
Total Dower Dissination (Note 6)	T <sub>A</sub> = +25°C	Б	2.02	W	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +70°C	$P_{D}$	1.30		
Thermal Desigtance Junction to Ambient (Note 6)	Steady state		62	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	42		
Thermal Resistance, Junction to Case (Note 6)	Steady state	$R_{ heta JC}$	9.3		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

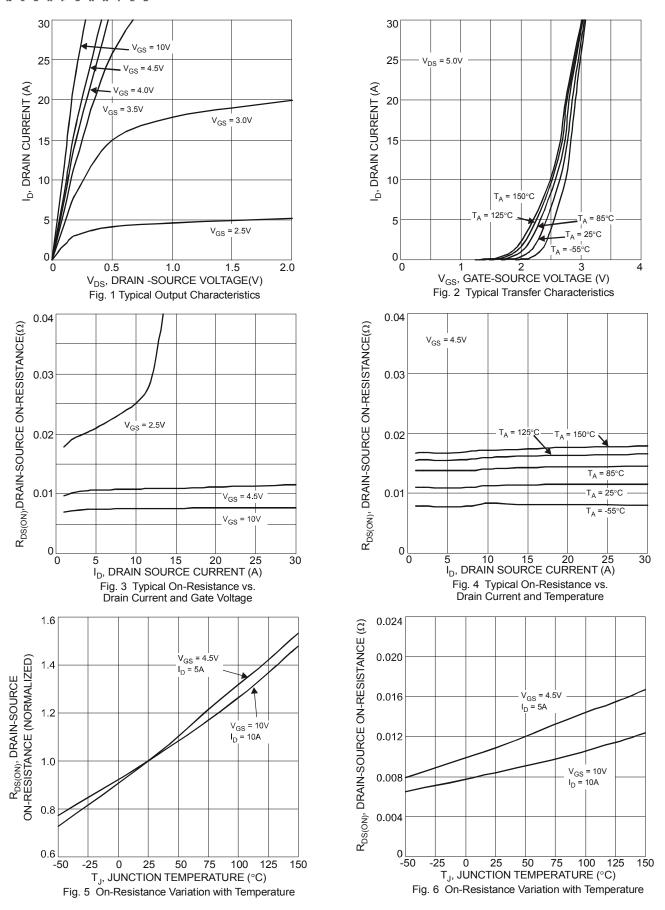
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)			-				
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.4	-	2.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		-	8	12	$\mathbf{m}\Omega$	$V_{GS} = 10V, I_D = 11A$	
Static Dialii-Source Oil-Resistance	R <sub>DS (ON)</sub>	-	12	16	111 22	$V_{GS} = 4.5V, I_D = 9A$	
Forward Transfer Admittance	Y <sub>fs</sub>	-	32	1	S	$V_{DS} = 5V, I_{D} = 12A$	
Diode Forward Voltage	$V_{SD}$	-	0.70	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	-	1415	-	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	-	119	-			
Reverse Transfer Capacitance	Crss	-	82	-			
Gate resistance	$R_g$	-	2.6	3.2	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	-	11.3	-			
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$	-	25.1	-	nC	V - 45V L - 40A	
Gate-Source Charge	Q <sub>gs</sub>	-	3.5	-	IIC	$V_{DS} = 15V, I_D = 12A$	
Gate-Drain Charge	$Q_{gd}$	-	3.6	-			
Turn-On Delay Time	t <sub>D(on)</sub>	-	4.8	-			
Turn-On Rise Time	tr	-	16.5	-	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V,	
Turn-Off Delay Time	$t_{D(off)}$	-	26.1	-		$R_L = 1.25\Omega$ , $R_G = 3\Omega$ ,	
Turn-Off Fall Time	t <sub>f</sub>	-	5.6	-			
Reverse Recovery Time	t <sub>rr</sub>	-	12.3	-	ns	1 404 41/44 5004/	
Reverse Recovery Charge	Q <sub>rr</sub>	-	10.4	-	nC	I <sub>F</sub> = 12A, di/dt = 500A/μs	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. 7.  $I_{AR}$  and  $E_{AR}$  rating are based on low frequency and duty cycles to keep  $T_J$  = +25°C

<sup>8.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>9.</sup> Guaranteed by design. Not subject to product testing.







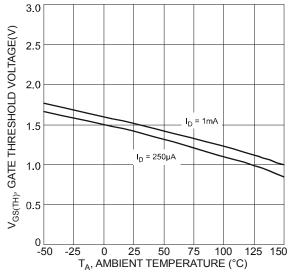
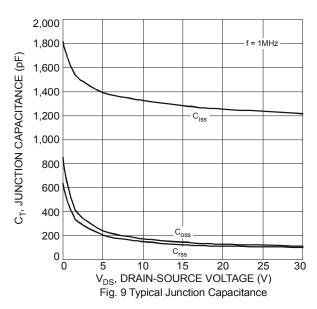
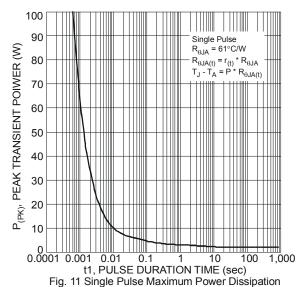
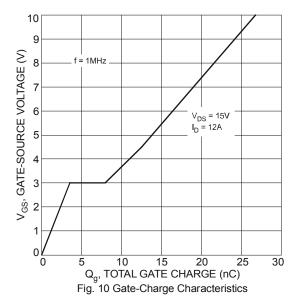


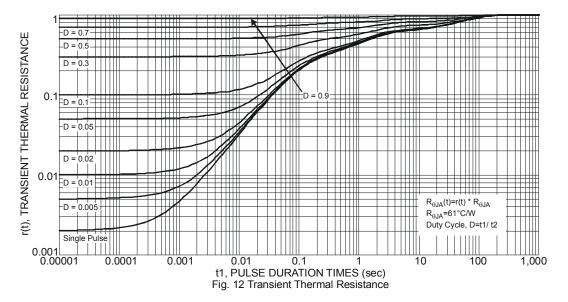
Fig. 7 Gate Threshold Variation vs. Ambient Temperature





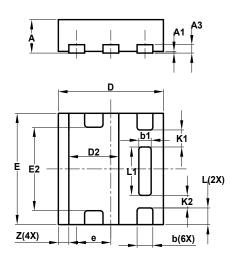






# **Package Outline Dimension**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

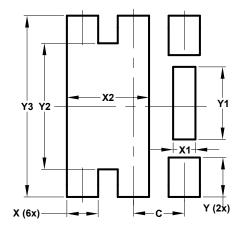


	U-DFN2020-6 Type E							
Dim	Min Max Typ							
Α	0.57	0.63	0.60					
A1	0	0.05	0.03					
A3	_	_	0.15					
b	0.25	0.35	0.30					
b1	0.185	0.285	0.235					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
Е	1.95	2.05	2.00					
E2	1.40	1.60	1.50					
е	-	_	0.65					
L	0.25	0.35	0.30					
L1	0.82	0.92	0.87					
K1	_	_	0.305					
K2	-	-	0.225					
Z	_	_	0.20					
All	All Dimensions in mm							



# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	0.650			
X	0.400			
X1	0.285			
X2	1.050			
Υ	0.500			
Y1	0.920			
Y2	1.600			
Y3	2.300			

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